AP013SN500MTB

N-Channel Enhancement Mode Power MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
500	500mΩ@10V	13A

Feature

- Self-aligned planar technology
- Low conduction loss

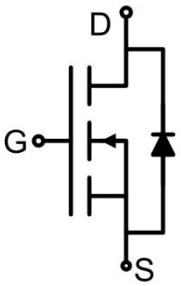
Application

- Uninterruptible power supply (UPS)
- Power factor correction (PFC)

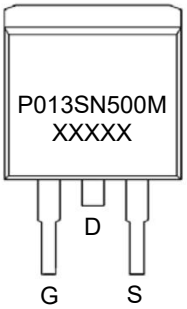
Package

TO-263AB

Circuit diagram



Marking



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N-Channel Enhancement Mode Power MOSFET

Absolute Maximum Ratings (T_C=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage (V_{GS} =0V)	V_{DS}	500	V
Gate-Source Voltage	V_{GS}	±30	V
Continuous Drain Current	I_D	13	A
Pulsed Drain Current[1)]	I_{DM}	52	A
Power Dissipation[2)]	P_D	31	W
Single pulse avalanche energy[3)]	E_{AS}	400	mJ
Thermal Resistance,Junction-to-Case	$R_{\theta JC}$	3.92	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55 ~ +150	℃

Electrical characteristics (T_J=25℃ unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} =0V, I_D =250μA	500			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =500V, V_{GS} =0V			1	μA
Gate-body leakage current	I_{GSS}	V_{DS} =0V, V_{GS} =±30V			±100	nA
Gate threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250μA	2		4	V
Drain-source on-resistance[4)]	$R_{DS(on)}$	V_{GS} =10V, I_D =6.5A		420	500	mΩ
Dynamic characteristics[5)]						
Input Capacitance	C_{iss}	V_{DS} =25V, V_{GS} =0V, f =1MHz		1175		pF
Output Capacitance	C_{oss}			176		
Reverse Transfer Capacitance	C_{rss}			6		
Total Gate Charge	Q_g	V_{DS} =400V, V_{GS} =10V, I_D =13A		22		nC
Gate-Source Charge	Q_{gs}			6.4		
Gate-Drain Charge	Q_{gd}			6.8		
Turn-on delay time	$t_{d(on)}$	V_{DS} =250V, V_{GS} =10V, I_D =13A R_G =25Ω		26		nS
Turn-on rise time	t_r			39		
Turn-off delay time	$t_{d(off)}$			87		
Turn-off fall time	t_f			42		
Source-Drain Diode characteristics						
Diode Forward Current	I_S				13	A
Diode Forward voltage	V_{SD}	V_{GS} =0V, I_S =13A			1.2	V
Reverse Recovery Time	t_{rr}	V_{GS} =0V, I_S =13A di/dt =100A/μs		334		nS
Reverse Recovery Charge	Q_{rr}			2.6		μC

Notes:

1) The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.

2) The power dissipation is limited by 150℃ junction temperature.

3) The EAS data shows Max. rating . L=4.1mH,I_{AS}=16A,V_{DD}=50V,R_G =25Ω, Starting T_J = 25 ºC.

4) The test condition is Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 1%.

5) Guaranteed by design, not subject to production testing.

Typical Characteristics

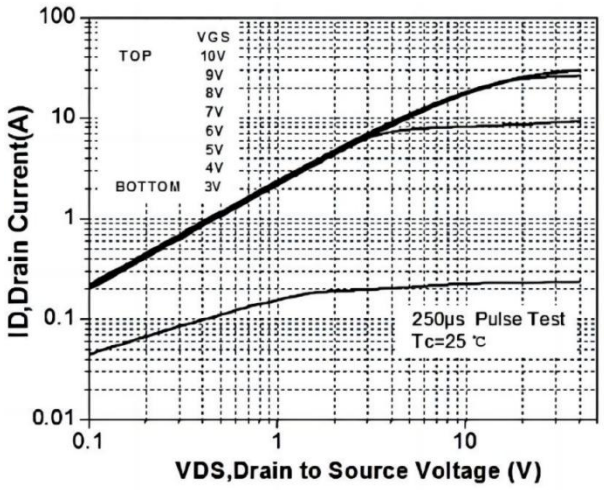


Figure 1. On-Region Characteristics

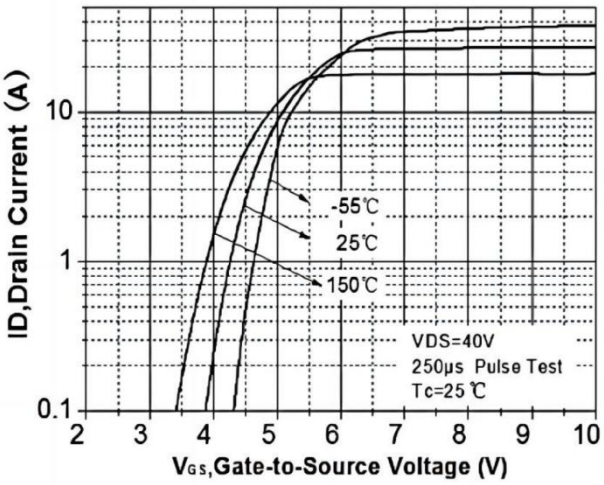


Figure 2. Transfer Characteristics

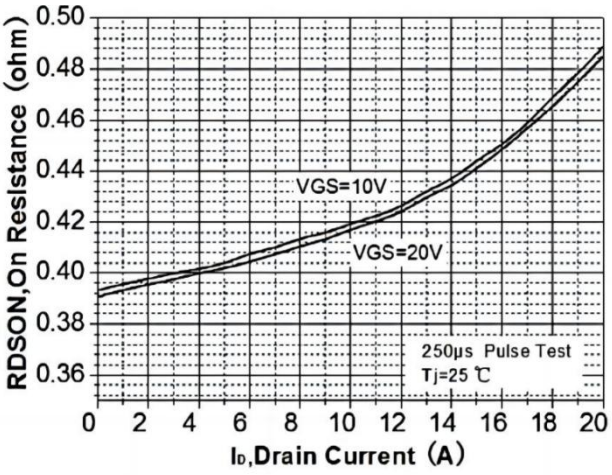


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

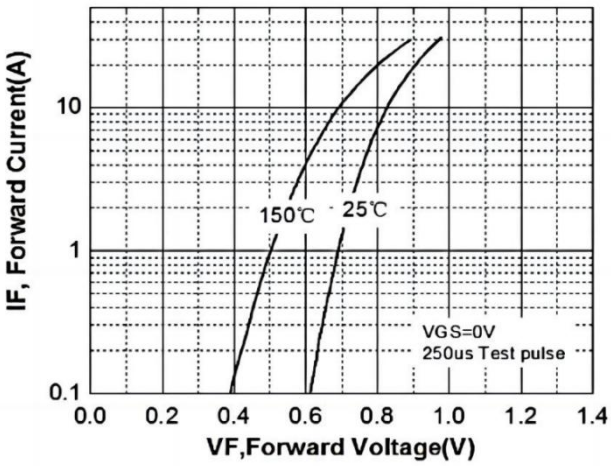


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

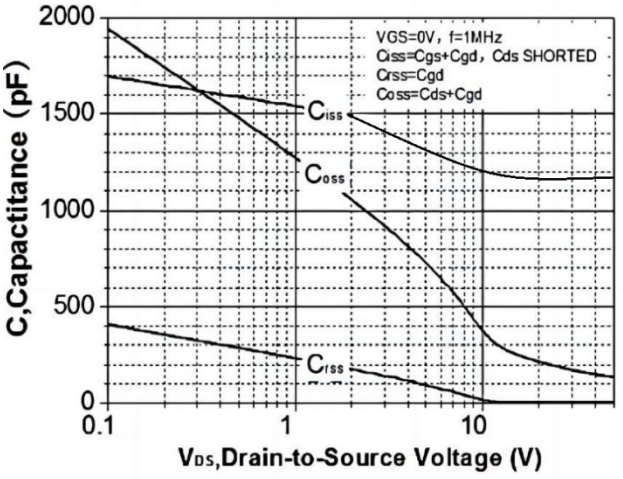


Figure 5. Capacitance Characteristics

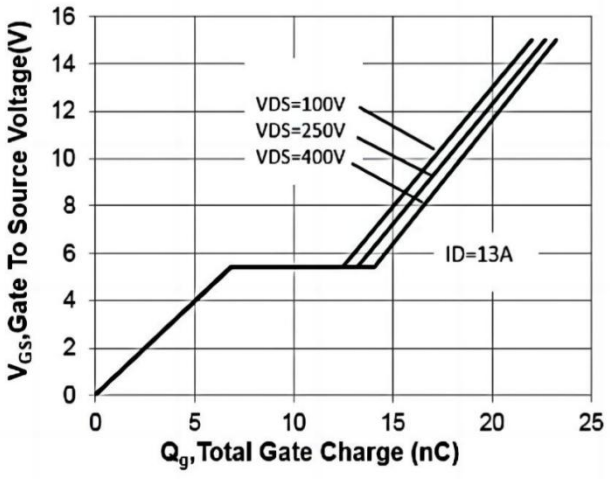


Figure 6. Gate Charge Characteristics

Typical Characteristics

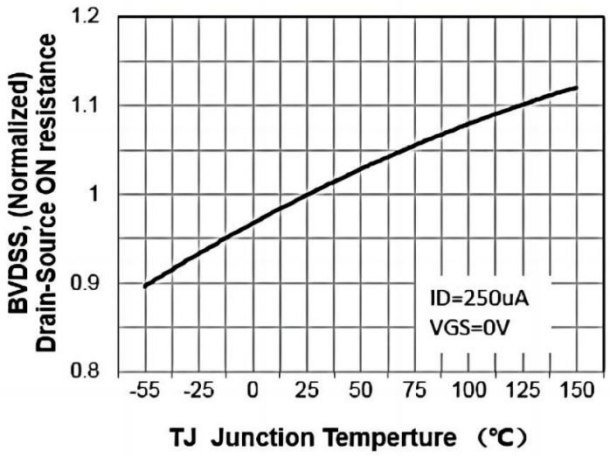


Figure 7. Breakdown Voltage Variation vs Temperature

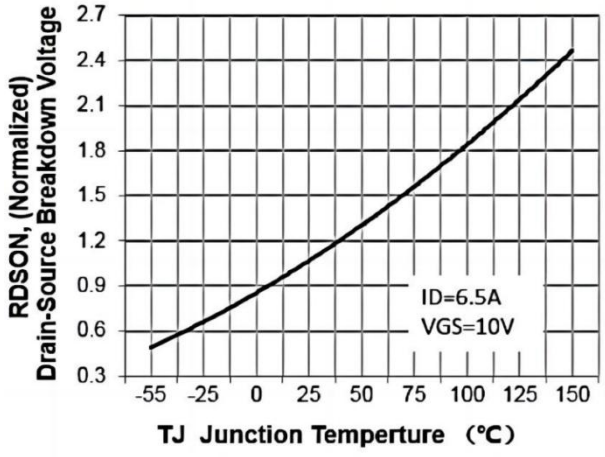


Figure 8. On-Resistance Variation vs Temperature

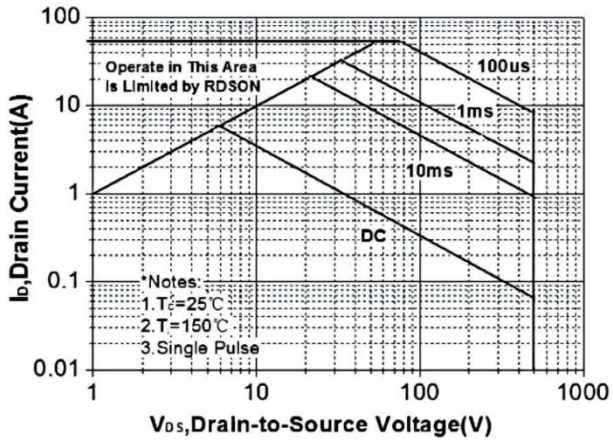


Figure 9. Maximum Safe Operating Area

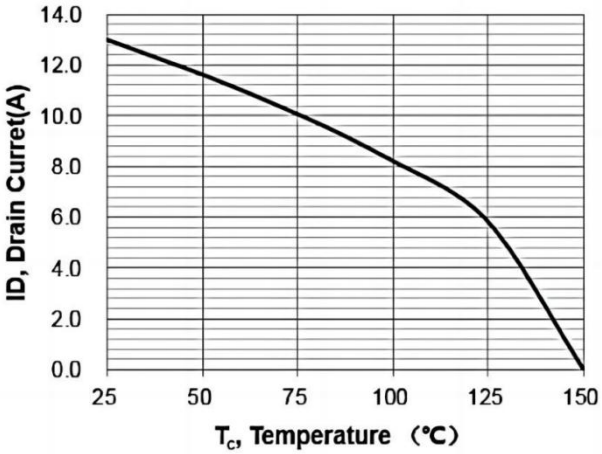


Figure 10. Maximum Drain Current vs Case Temperature

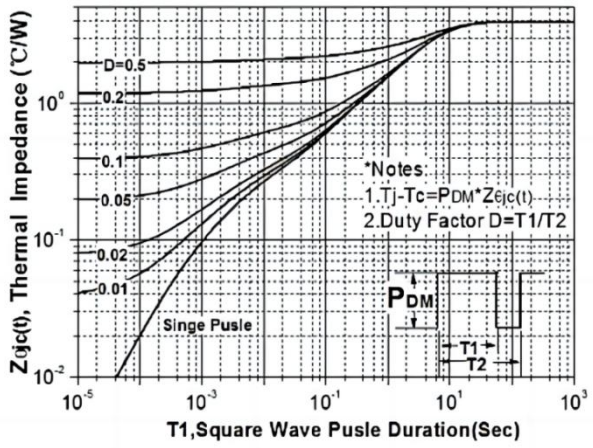
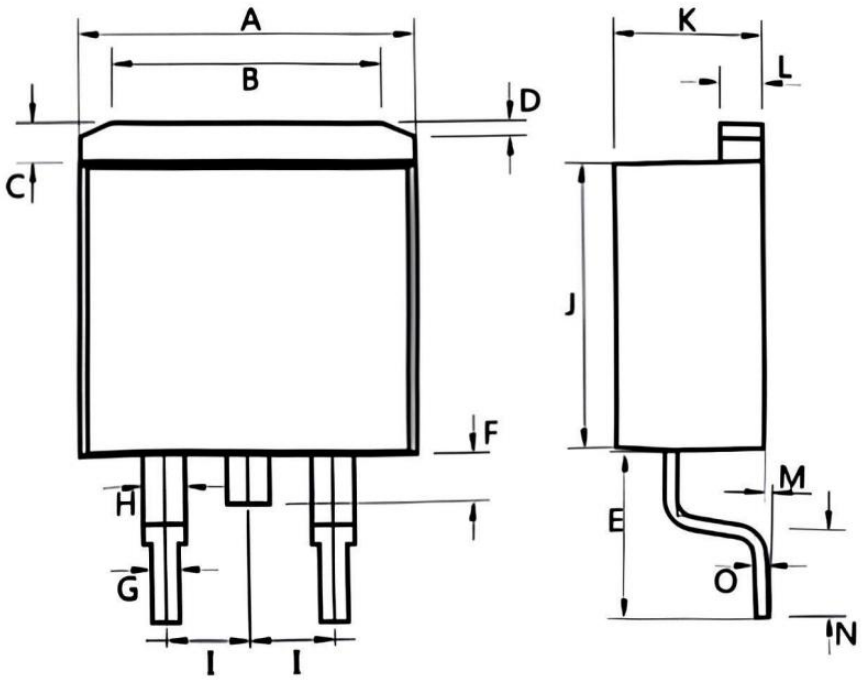


Figure 11. Transient Thermal Response Curve

TO-263AB Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	10.000	10.500	0.394	0.413
B	7.250	7.750	0.285	0.305
C	1.300	1.500	0.051	0.059
D	0.550	0.750	0.022	0.030
E	5.000	6.000	0.197	0.236
F	1.400	1.600	0.055	0.063
G	0.750	0.950	0.030	0.037
H	1.150	1.350	0.045	0.053
I	2.540 BSC		0.100 BSC	
J	8.400	8.600	0.331	0.339
K	4.400	4.600	0.173	0.181
L	1.250	1.450	0.049	0.057
M	0.020	0.100	0.001	0.004
N	2.400	2.800	0.094	0.110
O	0.350	0.450	0.014	0.018